

STRUCTURAL AND ELECTROOPTICAL PROPERTIES OF THE SILICON AFTER NEUTRON IRRADIATION AND HIGH TEMPERATURE TREATMENT

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The process of the defect formation, supporting oxide precipitation after neutron irradiation (10^{15} - 10^{19} n/cm²) and high temperature treatment (800 - 1000 °C) of Cz silicon wafers was investigated by the transmission electron microscopy. The influence of defect transformation on electrooptical silicon properties were studied.